

Claims 3 and 4 are amended by the present response to no longer recite any multiple dependencies. Further, subject matter of the canceled multiple dependencies is now set forth in new dependent claims 5-8.

The Abstract has also been amended by the present response to be in more proper format under United States practice.

The present application is believed to be in condition for a full and thorough examination on the merits. An early and favorable consideration of the present application is hereby respectfully requested.

Respectfully submitted,

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IN THE TITLE

--[HOT PLATE FOR SEMICONDUCTOR PRODUCING/EXAMINING DEVICE]

HOT PLATE FOR SEMICONDUCTOR MANUFACTURE AND TESTING

IN THE CLAIMS

3. (Amended) The hot plate for a semiconductor producing/examining device according to claim 1 [or 2],

wherein said ceramic substrate is subjected to an annealing treatment.

4. (Amended) The hot plate for a semiconductor producing/examining device according to [any of claims 1 to 3] claim 1,

wherein said ceramic substrate is subjected to a cold isostatic pressing process before it is sintered.

Claims 5-8 (New).--

IN THE ABSTRACT

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[An object of the present invention is to provide a] A hot plate for a semiconductor producing/examining device, in which hot plate, when an object to be heated such as a silicon wafer is heated in a state that the object is distanced by a certain distance from the heating

face, air is less likely to stagnate between the silicon wafer and the heating face and thus the object to be heated can be evenly heated. Specifically, the hot plate for a semiconductor producing/examining device [of the present invention comprises] includes a resistance heating element formed on a surface of a ceramic substrate or inside the ceramic substrate, wherein the glossiness of the heating face of [said] the ceramic substrate is 1.5% or more.--